## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Multiple sheets used when necessary)
SHEET 1 OF 1

	PTO/Sb/06 Equivalen
Application No.	10/568,227
Filing Date	May 17, 2006
First Named Inventor	Vivian Alberts
Art Unit	2895
Examiner	Singal, Ankush K.
Attorney Docket No.	DMKISCH 002APC

## U.S. PATENT DOCUMENTS

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Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
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## FOREIGN PATENT DOCUMENTS

1	TORCION TATER TO COMMENTO					
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>1</sup>

## NON PATENT LITERATURE DOCUMENTS

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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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